

Low-Cost, General-Purpose Silicon Photodiode

Optoelectronics Group

FPT720

General Description

The FPT720 is a low-cost, general-purpose, silicon photodiode encapsulated in a clear plastic T1 package.

Absolute Maximum Ratings

Maximum Temperature and Humidity

Operating Temperature	-40°C to +85°C
Storage Temperature	-55°C to +100°C
Pin Temperature (Soldering, 5 s)	230°C
Relative Humidity at 85°C	85%

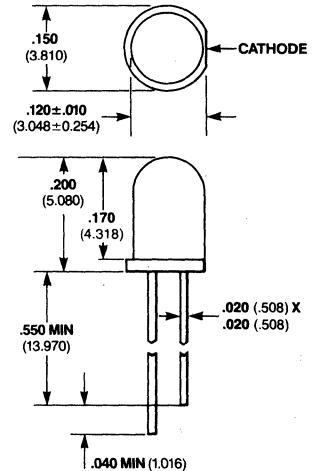
Maximum Power Dissipation

Total Dissipation at $T_A = 25^\circ\text{C}$	100 mW
Derate Linearly from 25°C	1.33 mW/°C

Maximum Voltage and Current

V_R Reverse Voltage	50 V
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Package Outline



Notes

All dimensions in inches **bold** and millimeters (parentheses)
Tolerance unless specified = $\pm .015$ ($\pm .381$)
Blue Dot on package side differentiates PHOTODIODE from PHOTO
EMITTER

Typical Electrical Characteristic

FPT720

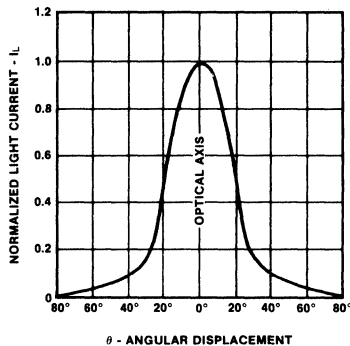
Electrical Characteristics $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV	Breakdown Voltage	50	120		V	$I_R = 10 \mu\text{A}$, $H \leq 0.1 \mu\text{W}/\text{cm}^2$
V_{OC}	Open-Circuit Voltage (Note)	380	400		mV	No Bias, $H = 20 \text{ mW}/\text{cm}^2$
I_R	Dark Current		0.3	35	nA	$V_R = -10 \text{ V}$, $H \leq 0.1 \mu\text{W}/\text{cm}^2$
I_L	Photo Current (Note)	15	25		μA	$V_R = -10 \text{ V}$, $H = 20 \text{ mW}/\text{cm}^2$
$I_{L(sc)}$	Short-Circuit Current (Note)	15	25		μA	No Bias, $H = 20 \text{ mW}/\text{cm}^2$
R (Tungsten)	Responsivity (Note)	0.6	1.0		$\mu\text{A}/\text{mW}/\text{cm}^2$	No Bias, $T_C = 2854^\circ\text{K}$
R @ 900 nm	Responsivity 900 nm		3.9		$\mu\text{A}/\text{mW}/\text{cm}^2$	No Bias, GaAs
C_O	Open-Circuit Capacitance		60		pF	$V_R = 0 \text{ V}$, $H \leq 0.1 \text{ mW}/\text{cm}^2$
C_R	Reversed Bias Capacitance		20		pF	$V_R = -10 \text{ V}$, $H \leq 0.1 \mu\text{W}/\text{cm}^2$
R_{max}	Responsivity (Absolute) at Spectral Peak		0.6		A/W	$V_R = 0 \text{ V}$, $\lambda = 800 \text{ nm}$
NEP	Noise Equivalent Power		1.0×10^{-14}		W	$V_R = -10 \text{ V}$, $\lambda = 800 \text{ nm}$, $\Delta f = 1.0 \text{ Hz}$
D	Detectivity		8.8×10^{12}		$\frac{\text{cm}\sqrt{\text{Hz}}}{\text{W}}$	$V_R = -10 \text{ V}$, $\lambda = 800 \text{ nm}$, $f = 1.0 \text{ kHz}$, $\Delta f = 1.0 \text{ Hz}$

Note

Irradiation source is an unfiltered Tungsten Lamp operated at 2854°K color temperature

Normalized Light Current vs Angular Displacement



Relative Spectral Response

